

Supporting Information

Effective defect passivation of CsPbBr₃ quantum dots using gallium cations toward the fabrication of bright perovskite LEDs

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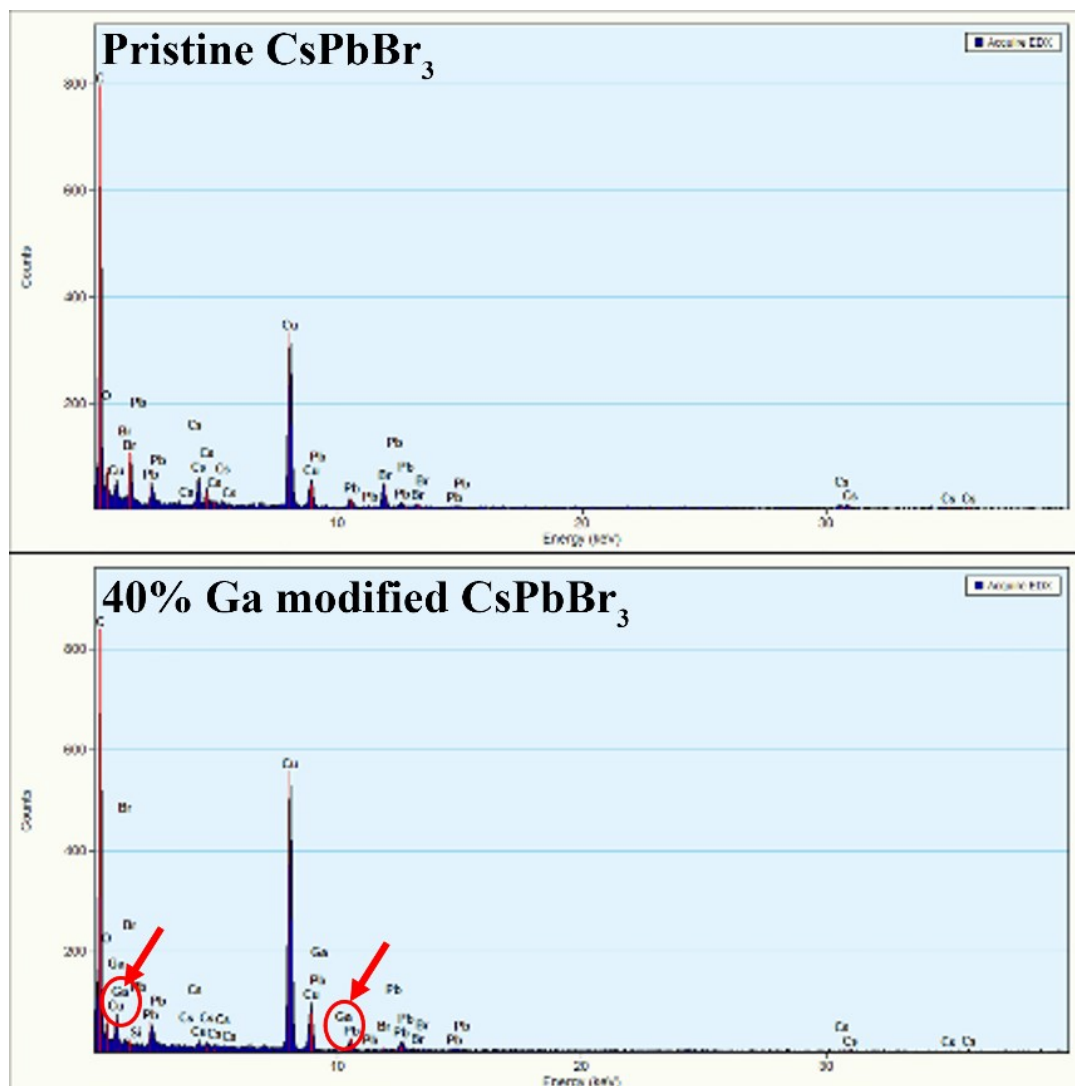


Fig. S1. Energy dispersive X-ray Spectrometry (EDS) spectra of the pristine and 40% Ga ions modified CsPbBr₃ QDs .

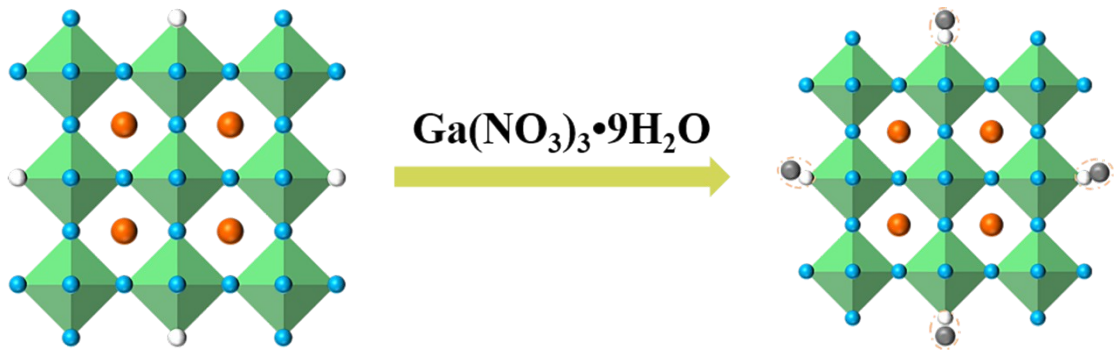


Fig. S2. Schematic diagram of the grain boundary passivation mechanism for Ga modified CsPbBr₃ QDs.

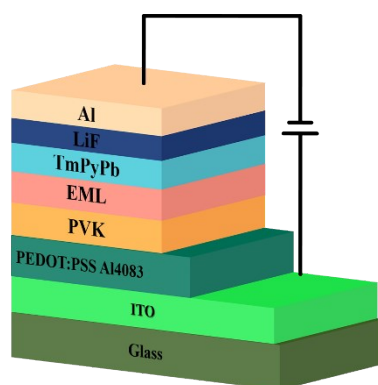


Fig. S3. Schematic device structure of the Perovskite QDs-based LEDs

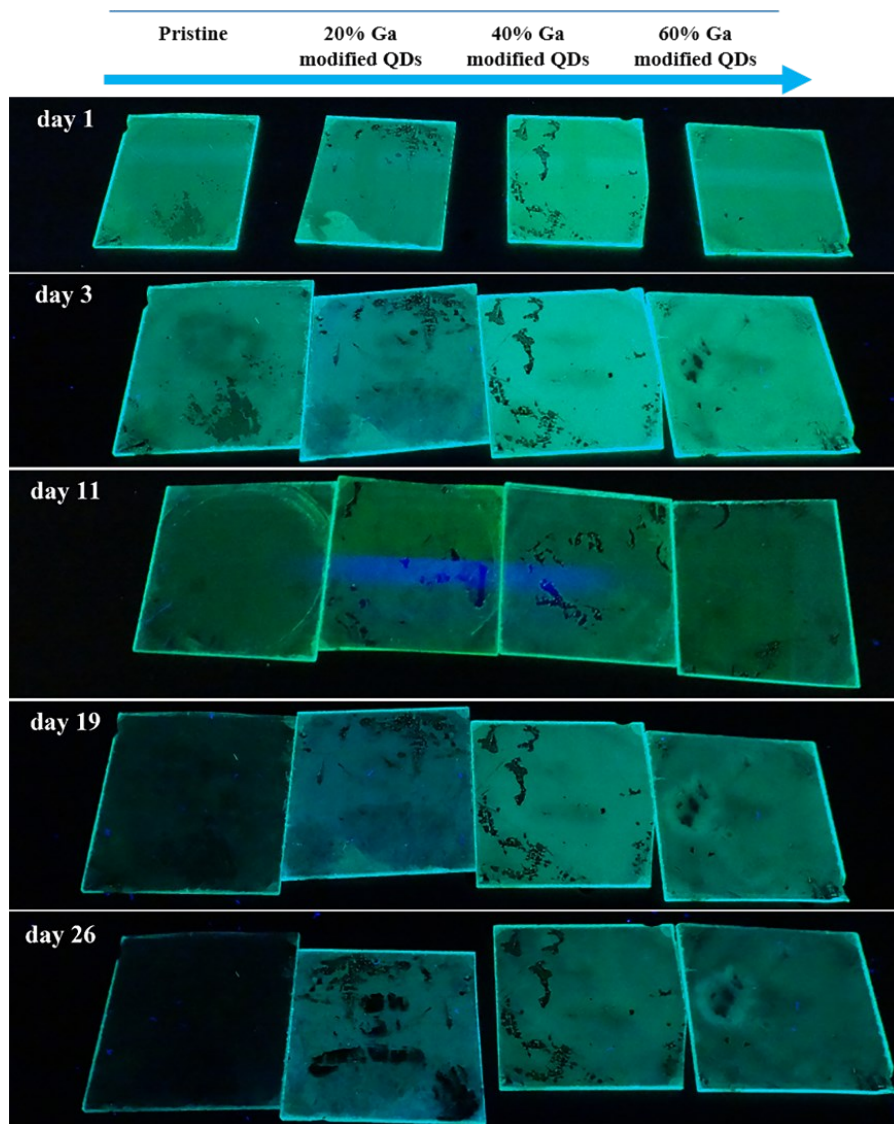


Fig. S4 PL emission photographs for different Ga ions modified CsPbBr₃ QDs coated on a glass slide taken under different UV irradiation time.

Table S1. The final Ga and Pb elemental concentrations of 40% Ga-modified CsPbBr₃ QDs (detection with ICP-OES)

Element	Ga	Pb
Concentration (mg/kg)	450.4	211296.8
Concentration (%)	0.05%	21.13%